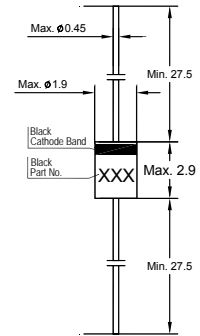


1N4531, 1N4532

SILICON EPITAXIAL PLANAR DIODES

Fast Switching Diode



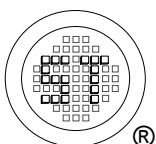
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Current	I_{FSM}	at $t = 1\text{ }\mu\text{s}$	4
		at $t = 1\text{ ms}$	1
		at $t = 1\text{ s}$	0.5
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_s	- 65 to + 200	$^\circ\text{C}$

Characteristics at $T_j = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	1	V
Reverse Current	I_R	at $V_R = 20\text{ V}$ 1N4531	25
		at $V_R = 50\text{ V}$ 1N4532	100
		at $V_R = 20\text{ V}, T_j = 150\text{ }^\circ\text{C}$ 1N4531	50
		at $V_R = 50\text{ V}, T_j = 150\text{ }^\circ\text{C}$ 1N4532	100
Diode Capacitance at $f = 1\text{ MHz}$	C_d	1N4531	4
		1N4532	2
Reverse Recovery Time at $I_F = 10\text{ mA}, I_R = 60\text{ mA}, R_L = 100\text{ }\Omega$	t_{rr}	1N4531	4
		1N4532	2
		at $I_F = 10\text{ mA}, I_R = 10\text{ mA}, R_L = 100\text{ }\Omega$ 1N4532	4
Forward Recovery Voltage at $I_F = 100\text{ mA}, t_r \leq 30\text{ ns}$	V_{fr}	3	V
Thermal Resistance from Junction to Ambient	R_{thJA}	350	K/W



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

Dated : 23/06/2007